

IN THE CLAIMS

Please cancel claim 21, without prejudice.

Please rewrite claim 22 as follows:

--22. (Amended) An electronic device having a substantially consistent gate voltage and a saturation mobility  $\mu$ , in the range of about 0.001 to about  $100 \text{ cm}^2/\text{V.s.}$ --

Please cancel claim 23 without prejudice.

Please rewrite claim 24 as follows:

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Cancella*  
--24. A device comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer, said device having a substantially consistent gate voltage and a saturation mobility lying in the range of about 0.001 to about  $1000 \text{ cm}^2/\text{V.s.}$ --

Please add new claim 28-33 as follows:

*E 2*  
--28. The electronic device of claim 22 which has a saturation mobility in the range of about 0.001 to about  $10 \text{ cm}^2/\text{V.s.}$

29. The electronic device of claim 22 which has a saturation mobility in the range of between about 0.1 to about  $1.00 \text{ cm}^2/\text{V.s.}$

30. The electronic device of claim 22 which is a transistor.

31. The device comprising a substantially exclusive polycrystalline Si:H or a polycrystalline and amorphous Si:H layer of claim 24 wherein said device has a saturation mobility lying in the range of about 0.001 to about  $500 \text{ cm}^2/\text{V.s.}$

32. A device obtainable according to a process for providing a semiconducting device comprising the steps of depositing a semiconducting layer onto a substrate situated in a vessel by means of heating a gas to a predetermined, dissociation temperature so that the gas dissociates into fractions, whereby those fractions subsequently condense on the substrate to

*Molecular  
beam  
process*